



Stud Diode

Rectifier Diode

SKN 130
SKR 130

Features

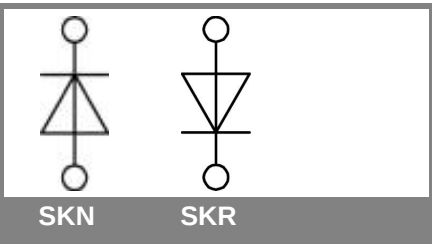
- Reverse voltages up to 1800 V
- Hermetic metal case with glass insulator
- Threaded stud ISO M12 (also 1/2 - 20 UNF, 3/8 - 24 UNF and M12 x 1,5)
- SKN: anode to stud, SKR: cathode to stud

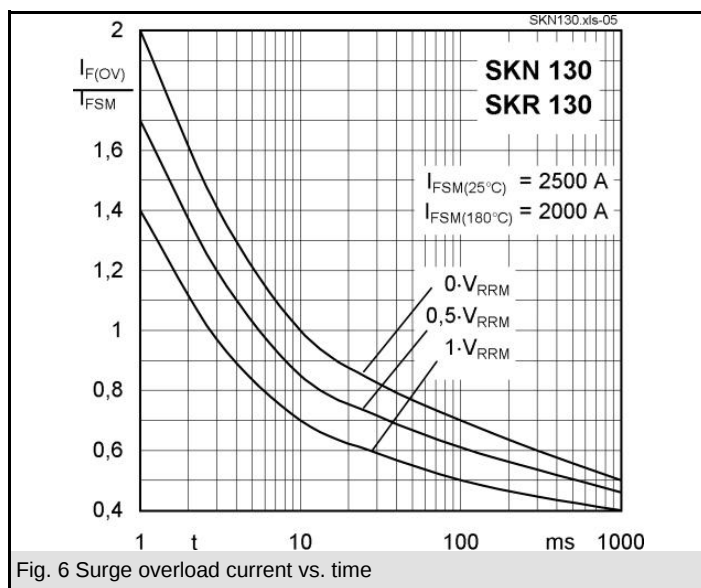
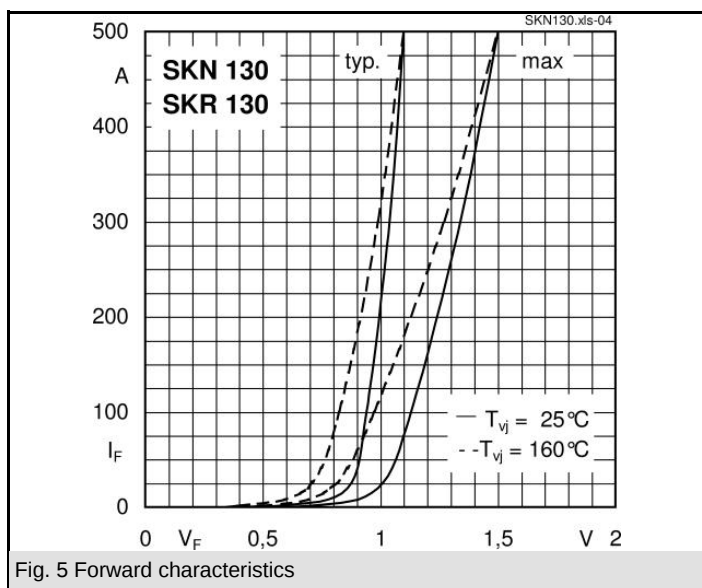
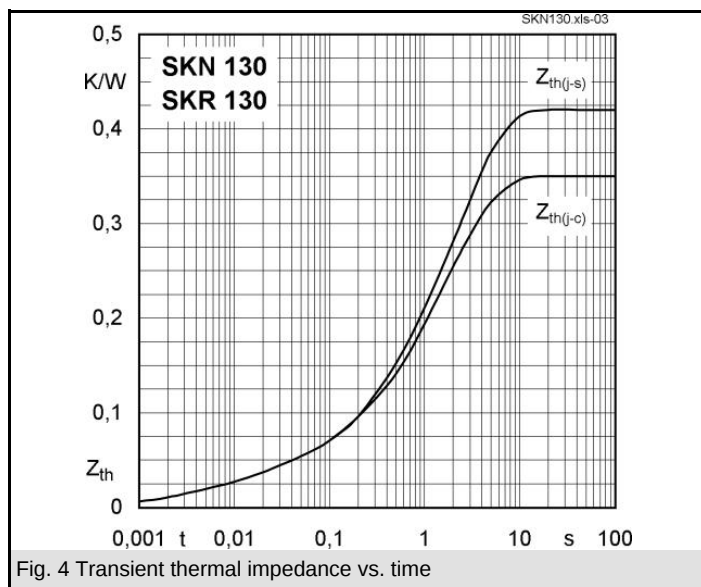
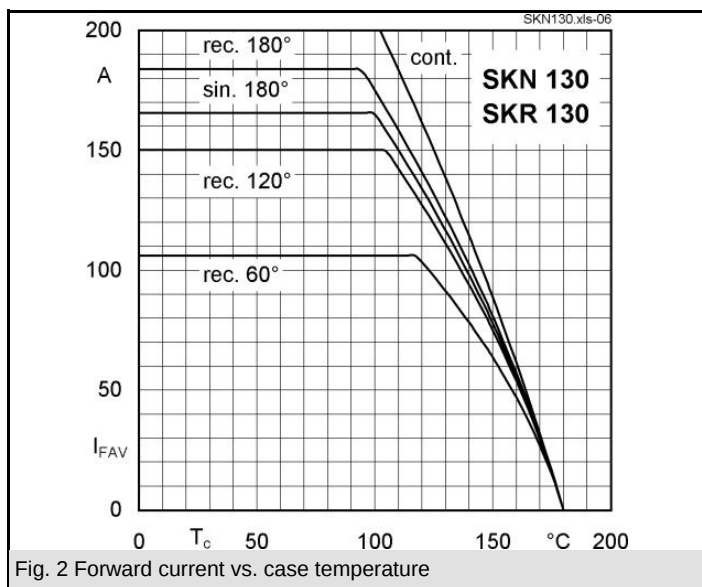
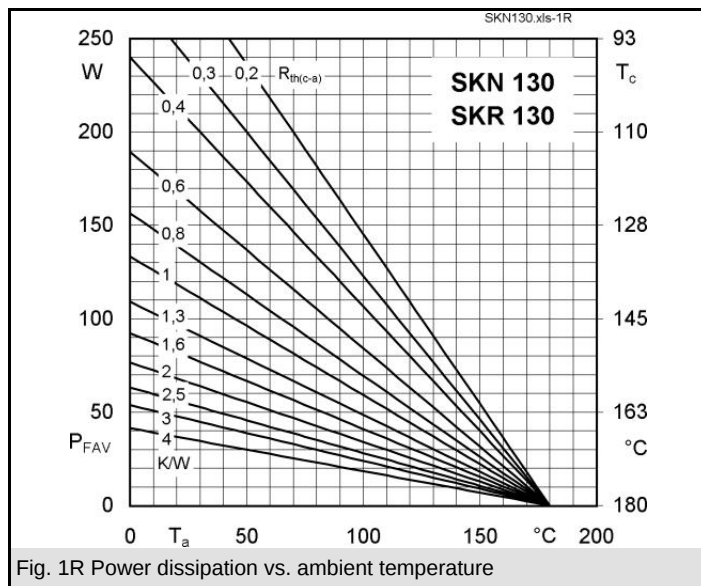
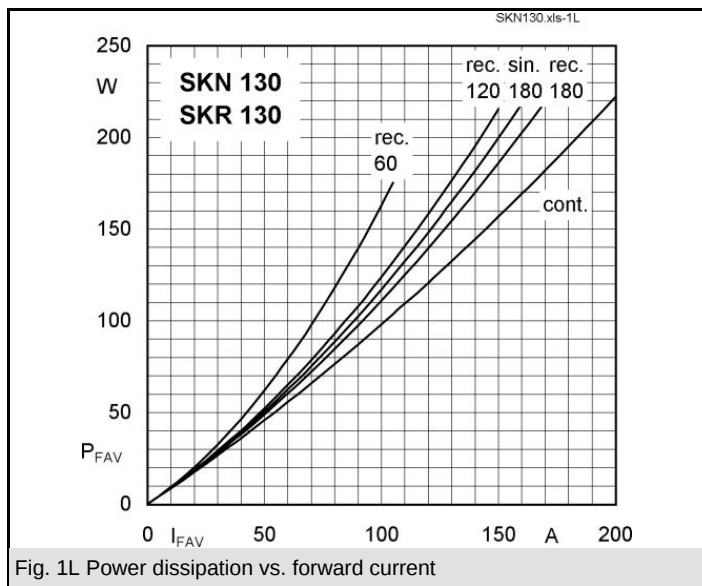
Typical Applications

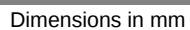
- All-purpose mean power rectifier diodes
- Cooling via heatsinks
- Non-controllable and half-controllable rectifier
- Free-wheeling diodes
- Recommended snubber network:
RC: 0,25 µF, 50 Ω, (P_R = 2 W),
R_P = 50 kΩ (P_R = 20 W)

V _{RSM} V	V _{RRM} V	I _{FRMS} = 260 A (maximum value for continuous operation)		
		I _{FAV} = 130 A (sin. 180; T _c = 125 °C)		
400	400	SKN 130/04	SKR 130/04	
800	800	SKN 130/08	SKR 130/08	
1200	1200	SKN 130/12	SKR 130/12	
1400	1400	SKN 130/14	SKR 130/14	
1600	1600	SKN 130/16	SKR 130/16	
1800	1800	SKN 130/18	SKR 130/18	

Symbol	Conditions	Values	Units
I _{FAV}	sin. 180; T _c = 100 °C	165	A
I _D	K 1,1; T _a = 45 °C; B2 / B6	160 / 225	A
	K 1,1F; T _a = 35 °C; B2 / B6	290 / 405	A
I _{FSM}	T _{vj} = 25 °C; 10 ms	2500	A
	T _{vj} = 180 °C; 10 ms	2000	A
i ² t	T _{vj} = 25 °C; 8,3 ... 10 ms	31000	A²s
	T _{vj} = 180 °C; 8,3 ... 10 ms	20000	A²s
V _F	T _{vj} = 25 °C; I _F = 500 A	max. 1,5	V
V _(TO)	T _{vj} = 180 °C	max. 0,85	V
r _T	T _{vj} = 180 °C	max. 1,3	mΩ
I _{RD}	T _{vj} = 180 °C; V _{RD} = V _{RRM}	max. 22	mA
Q _{rr}	T _{vj} = 160 °C; - di _F /dt = 10 A/µs	120	µC
R _{th(j-c)}		0,35	K/W
R _{th(c-s)}		0,08	K/W
T _{vj}		- 40 ... + 180	°C
T _{stg}		- 55 ... + 180	°C
V _{isol}		-	V~
M _s	to heatsink	10	Nm
a		5 * 9,81	m/s²
m	approx.	100	g
Case		E 14	







Case E 14 (IEC 60191: A 9 MA modified; JEDEC: DO-205 AC)

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